TOSHIBA Field Effect Transistor Silicon P-Channel MOS Type (U-MOSIV)

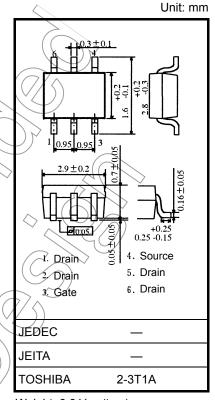
## **TPC6108**

# Notebook PC Applications Portable Equipment Applications

- Small footprint due to small and thin package
- Low drain-source ON-resistance:  $R_{DS (ON)} = 50 \text{ m}\Omega \text{ (typ.)}$
- High forward transfer admittance: |Yfs| = 7.4 S (typ.)
- Low leakage current:  $I_{DSS} = -10 \mu A \text{ (max) (V}_{DS} = -30 \text{ V)}$
- Enhancement mode:  $V_{th} = -0.8$  to -2.0 V ( $V_{DS} = -10$  V,  $I_D = -1$  mA)

#### Absolute Maximum Ratings (Ta = 25°C)

| Characteristics  |                 |                    | Symbol           | Rating      | Upit      |
|--|-----------------|--------------------|------------------|-------------|-----------|
| Drain-source voltage   |                 |                    | $V_{DSS}$        | -30         | $\bigvee$ |
| Drain-gate voltage ( $R_{GS} = 20 \text{ k}\Omega$ )                             |                 |                    | $V_{DGR}$        | _30(        | y         |
| Gate-source voltage  |                 |                    | V <sub>GSS</sub> | ±20         | > V       |
| Drain current  | DC              | (Note 1)           | I <sub>D</sub>   | -4.5        | Α         |
|  | Pulse           | (Note 1)           | I <sub>DP</sub>  | -18         | A         |
| Drain power dissipation (t = 5 s) (Note 2a)                                      |                 |                    | Pg               | 2.2         | W         |
| Drain power dissip   | ation (t = 5 s) | PD                 | 0.7              | << <b>v</b> |           |
| Single-pulse avala   | nche energy     | (E <sub>AS</sub> ) | 1.3              | mJ/         |           |
| Avalanche current  |                 |                    | 1AR              | -2.25       | Α         |
| Repetitive avalanche energy<br>Single-device value at dual operation<br>(Note 4) |                 |                    | EAR              | 0.22        | Jw7       |
| Channel temperatu  | ure             | T <sub>ch</sub>    | 150              | °C          |           |
| Storage temperatu  | ire range       | T <sub>stg</sub>   | -55 to 150       | °C          |           |
|  | 1 ( )           |                    |                  | ( ) / / / / |           |



Weight: 0.011 g (typ.)

Note: Using continuously under heavy loads (e.g. the application of high temperature/current/voltage and the significant change in temperature, etc.) may cause this product to decrease in the reliability significantly even if the operating conditions (i.e. operating temperature/current/voltage, etc.) are within the absolute maximum ratings. Please design the appropriate reliability upon reviewing the Toshiba Semiconductor Reliability Handbook ("Handling Precautions"/Derating Concept and Methods) and individual reliability data (i.e. reliability test report and estimated failure rate, etc).

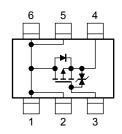
#### **Thermal Characteristics**

|  | V                      |       |      |
|--|------------------------|-------|------|
| Characteristics  | Symbol                 | Max   | Unit |
| Thermal resistance, channel to ambient (t = 5 s) (Note 2a)   | R <sub>th (ch-a)</sub> | 56.8  | °C/W |
| Thermal resistance, channel to ambient $(t = 5 s)$ (Note 2b) | R <sub>th (ch-a)</sub> | 178.5 | °C/W |

Note: For Notes 1 to 4, see page 3.

Caution: This transistor is an electrostatic-sensitive device. Handle with care.

#### **Circuit Configuration**

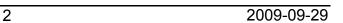


### **Electrical Characteristics (Ta = 25°C)**

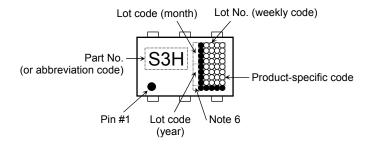
| Ch  | naracteristic | Symbol               | Test Condition  | Min    | Тур.                                   | Max      | Unit |
|---|---------------|----------------------|---|--------|--|----------|------|
| Gate leakage current                            |               | I <sub>GSS</sub>     | $V_{GS} = \pm 16 \text{ V}, V_{DS} = 0 \text{ V}$                 | _      | _                                      | ±10      | μΑ   |
| Drain cut-off current                           |               | I <sub>DSS</sub>     | $V_{DS} = -30 \text{ V}, V_{GS} = 0 \text{ V}$                    | _      | _                                      | -10      | μА   |
| Drain-source breakdown voltage                  |               | V (BR) DSS           | $I_D = -10 \text{ mA}, V_{GS} = 0 \text{ V}$                      | -30    | _                                      | _        | V    |
|   |               | V <sub>(BR)DSX</sub> | $I_D = -10 \text{ mA}, V_{GS} = 20 \text{ V}$                     | 15     | _                                      | _        | V    |
| Gate threshold voltage                          |               | V <sub>th</sub>      | $V_{DS} = -10 \text{ V}, I_D = -1 \text{ mA}$                     | (+0.8) | \\\\\\\\\\\\\\\\\\\\\\\\\\\\\\\\\\\\\\ | -2.0     | V    |
| Drain-source ON-resistance                      |               | R <sub>DS</sub> (ON) | $V_{GS} = -4.5 \text{ V}, I_D = -2.2 \text{ A}$                   |        | 75                                     | 100      | mΩ   |
|   |               | R <sub>DS</sub> (ON) | $V_{GS} = -10 \text{ V}, I_D = -2.2 \text{ A}$                    | / A    | 50                                     | 60       |      |
| Forward transfer admittance                     |               | Y <sub>fs</sub>      | $V_{DS} = -10 \text{ V}, I_D = -2.2 \text{ A}$                    | 3.7    | 7.4                                    | _        | S    |
| Input capacitance                               |               | C <sub>iss</sub>     |   | _      | 570                                    |          |      |
| Reverse transfer capacitance                    |               | C <sub>rss</sub>     | $V_{DS} = -10 \text{ V}, V_{GS} = 0 \text{ V}, f = 1 \text{ MHz}$ | _      | 75                                     | _        | pF   |
| Output capacitance                              |               | Coss                 |   | _      | 85                                     | _        |      |
| Switching time                                  | Rise time     | t <sub>r</sub>       | V <sub>GS</sub> 0 V   <sub>D</sub> = 2.2 A                        | - (    | 3.5                                    | <u> </u> | - ns |
|   | Turn-on time  | t <sub>on</sub>      | -10 V   |        | 12                                     | ) —      |      |
|   | Fall time     | t <sub>f</sub>       | V <sub>DD</sub> ≈-15 V  | 7      | 21                                     |          |      |
|   | Turn-off time | t <sub>off</sub>     | Duty $\leq$ 1%, $t_W = 10 \mu s$                                  |        | 70                                     | _        |      |
| Total gate charge (gate-source plus gate-drain) |               | Qg                   | V <sub>DD</sub> ≈ -24 V, V <sub>G</sub> s ≈ -10 V,                |        | 13                                     |          |      |
| Gate-source charge1                             |               | Q <sub>gs1</sub>     | Ip = -4.5 A   | _      | 1.8                                    | _        | nC   |
| Gate-drain ("Miller") charge                    |               | Q <sub>gd</sub>      | ))  | _      | 2.5                                    | _        |      |

## Source-Drain Ratings and Characteristics (Ta = 25°C)

| Characteristic                       | Symbol             | Test Condition                                 | Min | Тур. | Max | Unit |
|--------------------------------------|--------------------|--|-----|------|-----|------|
| Drain reverse current Pulse (Note 1) | / I <sub>DRP</sub> | (7)\\ -  | _   | _    | -18 | Α    |
| Forward voltage (diode)              | V <sub>DSF</sub>   | $I_{DR} = 4.5 \text{ A}, V_{GS} = 0 \text{ V}$ | _   | _    | 1.2 | V    |



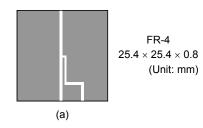
#### Marking (Note 5)

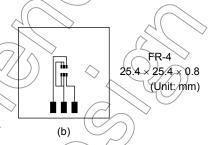


Note 1: Ensure that the channel temperature does not exceed 150°C.

Note 2: (a) Device mounted on a glass-epoxy board (a) (t = 5 s)

(b) Device mounted on a glass-epoxy board (b) (t = 5 s)





Note 3:  $V_{DD} = -24 \text{ V}$ ,  $T_{ch} = 25^{\circ}\text{C}$  (initial), L = 0.2 mH,  $R_G = 25 \Omega$ ,  $I_{AR} = -2.25 \text{ A}$ 

Note 4: Repetitive rating: pulse width limited by max channel temperature

Note 5: • to the lower left of the Part No. marking indicates Pin 1.

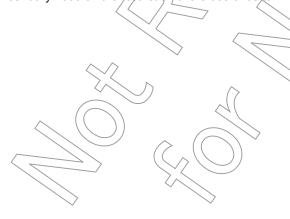
Note 6 A dot marking identifies the indication of product Labels.

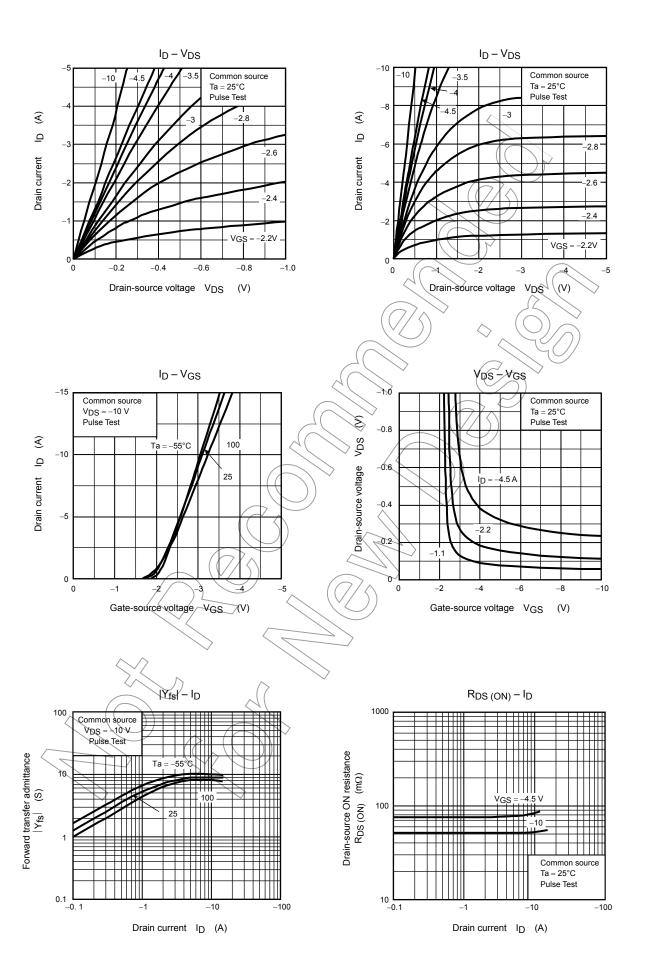
Without a dot: [[Pb]]/INCLUDES > MCV

With a dot: [[G]]/RoHS COMPATIBLE or [[G]]/RoHS [[Pb]]

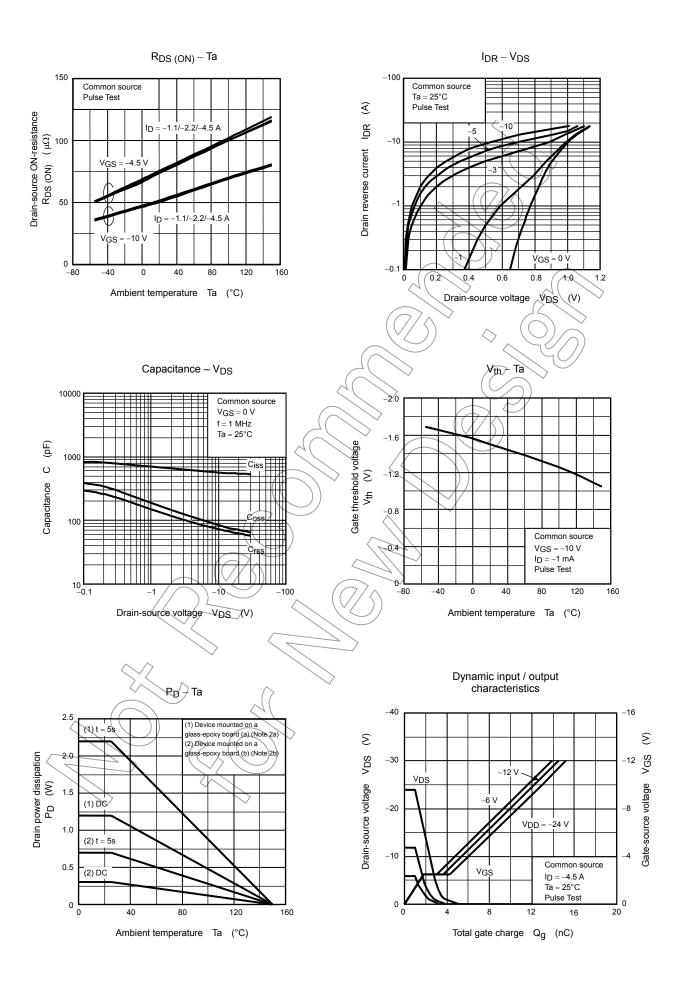
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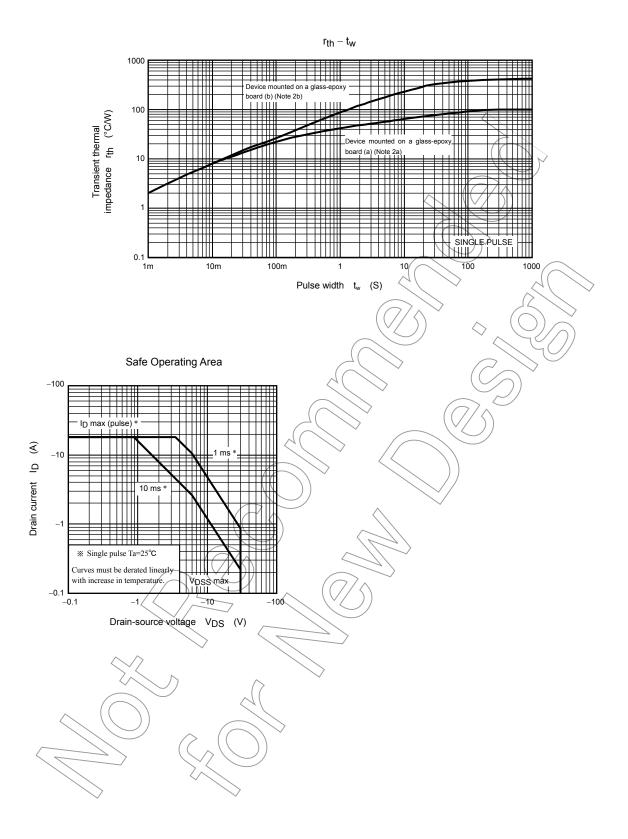
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